

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI FMB150 is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	16 A
V_{CB0}	60 V
V_{CEO}	25 V
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	230 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.1 °C/W

PACKAGE STYLE .500 4L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.125 / 3.18	
C	.245 / 6.22	.255 / 6.48
D	.720 / 18.28	.730 / 18.54
E	.125 / 3.18	
F	.970 / 24.64	.980 / 24.89
G	.495 / 12.57	.505 / 12.83
H	.003 / 0.08	.007 / 0.18
I	.090 / 2.29	.110 / 2.79
J	.150 / 3.81	.175 / 4.45
K	.280 / 7.11	
L	.980 / 24.89	1.050 / 26.67

ORDER CODE: ASI10588

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 100 mA	60			V
BV_{CER}	I _C = 100 mA R _{BE} = 10 Ω	55			V
BV_{CEO}	I _C = 100 mA	25			V
BV_{EBO}	I _E = 20 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	20		150	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			140	pF
P_G η_C	V _{CC} = 28 V P _{OUT} = 150 W f = 108 MHz	9.0	65		dB %